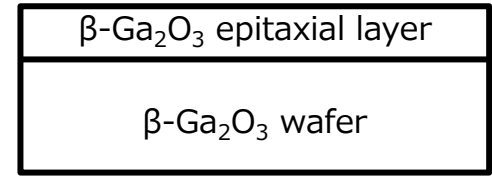


Standard specifications of 10×15 mm² β-Ga₂O₃ (010) epitaxial wafer (by MBE)

Epitaxial layer

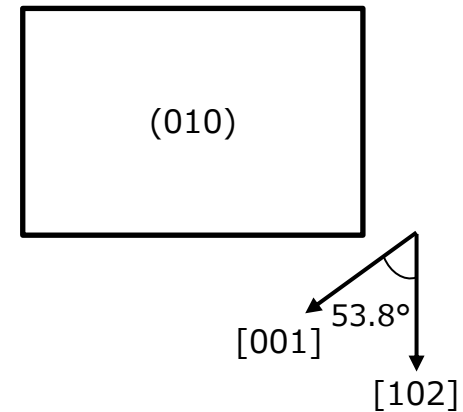
Items	Specifications	
Dopant	Si (n-type)	Undoped (semi-insulating)
Doping concentration (cm ⁻³) <small>*Selectable within the specified range.</small>	Specify a value between 1×10 ¹⁷ and 2×10 ¹⁸	-
Thickness (μm) <small>*Selectable in 1 μm increments.</small>	Specify a value between 0.1 and 0.5	



Cross section of β-Ga₂O₃ epitaxial wafer

Wafer

Items	Specifications	
Dopant	Sn (n-type)	Fe (semi-insulating)
Doping concentration (cm ⁻³)	Using the range of 1–9×10 ¹⁸	-
Resistivity (Ω·cm)	-	≥ 10 ¹⁰
Orientation	(010)	
Size (mm ²)	10×15	
Thickness (mm)	0.5	
XRD FWHM (arcsec)	≤ 150	
Off set angle (degree)	0 ± 1	



Orientation



Remarks

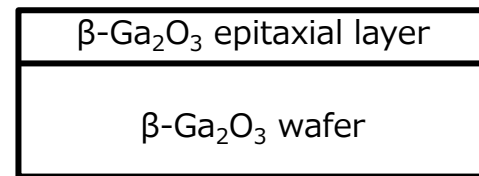
- 1 These products must be used for research and development purposes only.
- 2 The substrates must not be used as a seed crystal.
- 3 The specifications are subject to change without notice.

Standard specifications of

10×15 mm² β-(Al_xGa_{1-x})₂O₃ (010) epitaxial wafer (by MBE)

Epitaxial layer

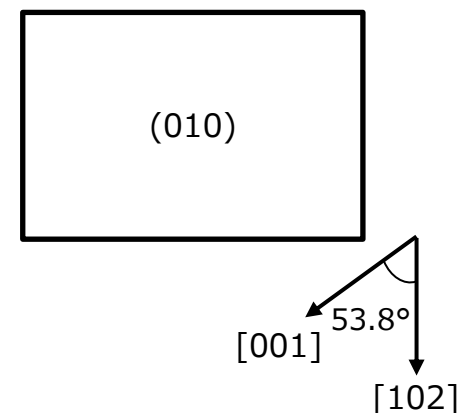
Items	Specifications
Al mole fraction	$x \leq 0.21$
Dopant	Si (n-type)
Doping concentration (cm ⁻³)	$\leq 1 \times 10^{18}$
Thickness (nm)	≤ 30



Cross section of β-Ga₂O₃ epitaxial wafer

Wafer

Items	Specifications	
Dopant	Sn (n-type)	Fe (semi-insulating)
Doping concentration (cm ⁻³)	Using the range of 1–9×10 ¹⁸	-
Resistivity (Ω·cm)	-	$\geq 10^{10}$
Orientation	(010)	
Size (mm ²)	10×15	
Thickness (mm)	0.5	
XRD FWHM (arcsec)	≤ 150	
Off set angle (degree)	0 ± 1	



Orientation



Remarks

1 These products must be used for research and development purposes only.

2 The substrates must not be used as a seed crystal.

3 The specifications are subject to change without notice.